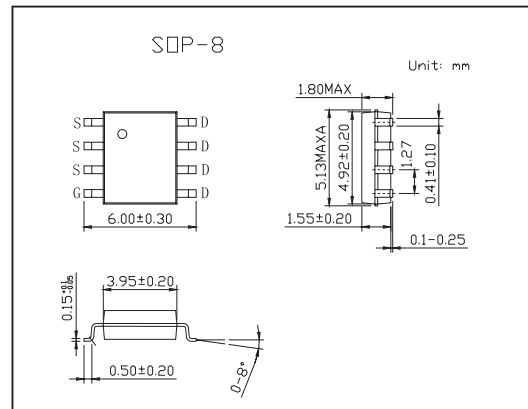
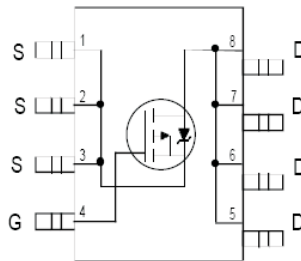


HEXFET[®] Power MOSFET

KRF7204

■ Features

- Advanced Process Technology
- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Continuous Drain Current, Vgs @ 10V @ TA = 25°C	I _D	-5.3	A
Continuous Drain Current, Vgs @ 10V @ TA = 70°C	I _D	-4.2	
Pulsed Drain Current *1	I _{DM}	-21	
Power Dissipation @T _C = 25°C	P _D	2.5	W/°C
Linear Derating Factor		0.02	V
Gate-to-Source Voltage	V _{GS}	± 12	V/nS
Peak Diode Recovery dv/dt *2	dv/dt	-1.7	W
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to + 150	°C
Maximum Junction-to-Ambient *3	R _{θJA}	50	°C/W



*1 Repetitive rating; pulse width limited by max. junction temperature.

*2 I_{SD} ≤ -5.3A, di/dt ≤ 90A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C

*3 Surface mounted on FR-4 board, t ≤ 10sec.

KRF7204

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250A$	-20			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	$I_D = -1mA, \text{Reference to } 25^\circ C$		-0.022		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -5.3A^{*1}$			0.060	Ω
		$V_{GS} = -4.5V, I_D = -2.0A^{*1}$			0.10	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1.0		-2.5	V
Forward Transconductance	g_{fs}	$V_{DS} = -15V, I_D = -5.3A^{*1}$		7.9		S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-2.5	μA
		$V_{DS} = -16V, V_{GS} = 0V, T_J = 125^\circ C$			-250	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = -12V$			-100	nA
Gate-to-Source Reverse Leakage		$V_{GS} = 12V$			100	
Total Gate Charge	Q_g	$I_D = -5.3A$ $V_{DS} = -10V$ $V_{GS} = -10V,^{*1}$		25		nC
Gate-to-Source Charge	Q_{gs}			5.0		
Gate-to-Drain ("Miller") Charge	Q_{gd}			8.0		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10V$ $I_D = -1.0A$ $R_G = 6.0 \Omega$ $R_D = 10 \Omega^{*1}$		14	30	ns
Rise Time	t_r			26	60	
Turn-Off Delay Time	$t_{d(off)}$			100	150	
Fall Time	t_f			68	100	
Internal Source Inductance	L_S	Between lead, 6mm(0.25in.) from package and center of die contact 		2.5		nH
Internal Drain Inductance	L_D			4.0		
Input Capacitance	C_{iss}	$V_{GS} = 0V$ $V_{DS} = -10V$ $f = 1.0MHz$		860		pF
Output Capacitance	C_{oss}			750		
Reverse Transfer Capacitance	C_{rss}			230		
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 			-2.5	A
Pulsed Source Current (Body Diode) *2	I_{SM}				-15	
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = -1.25A, V_{GS} = 0V^{*1}$			-1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = -2.4A$ $di/dt = 100A/\mu s^{*1}$		85	100	ns
Reverse Recovery Charge	Q_{rr}			77	120	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

*1 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

*2 Repetitive rating; pulse width limited by max